

N-Ch 60V Fast Switching MOSFETs

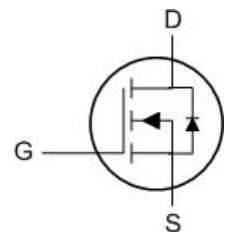
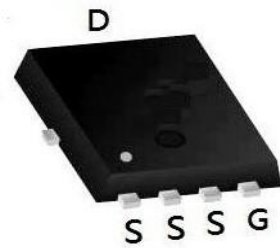

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

| BVDSS | R _{DS(on)} | I _D |
|-------|---------------------|----------------|
| 60V | 24mΩ | 30A |

Description

The XXW30N06 is the high cell density trenched N-ch MOSFETs, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications. The XXW30N06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3X3-8 Pin Configuration

Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|---------------------------------------|--|------------|-------|
| V _{DS} | Drain-Source Voltage | 60 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| I _D @T _C =25°C | Continuous Drain Current, V _{GS} @ 10V ¹ | 30 | A |
| I _D @T _C =100°C | Continuous Drain Current, V _{GS} @ 10V ¹ | 15 | A |
| I _{DM} | Pulsed Drain Current ² | 60 | A |
| EAS | Single Pulse Avalanche Energy ³ | 50 | mJ |
| I _{AS} | Avalanche Current | 30 | A |
| P _D @T _A =25°C | Total Power Dissipation ⁴ | 20 | W |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| T _J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|------------------|--|------|------|------|
| R _{θJA} | Thermal Resistance Junction-Ambient ¹ | --- | 62 | °C/W |

N-Ch 60V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|------------------------------|--|--|------|-------|-----------|----------------------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0V, I_D=250\mu A$ | 60 | --- | --- | V |
| $\Delta BV_{DSS}/\Delta T_J$ | BV_{DSS} Temperature Coefficient | Reference to 25°C , $I_D=1\text{mA}$ | --- | 0.063 | --- | $V/^\circ\text{C}$ |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance ² | $V_{GS}=10V, I_D=15A$ | --- | 24 | 30 | m Ω |
| | | $V_{GS}=4.5V, I_D=10A$ | --- | 25 | 38 | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS}=V_{DS}, I_D=250\mu A$ | 1.2 | --- | 2.5 | V |
| $\Delta V_{GS(th)}$ | $V_{GS(th)}$ Temperature Coefficient | | --- | -5.24 | --- | $\text{mV}/^\circ\text{C}$ |
| I_{DSS} | Drain-Source Leakage Current | $V_{DS}=48V, V_{GS}=0V, T_J=25^\circ\text{C}$ | --- | --- | 1 | μA |
| | | $V_{DS}=48V, V_{GS}=0V, T_J=55^\circ\text{C}$ | --- | --- | 5 | |
| I_{GSS} | Gate-Source Leakage Current | $V_{GS}=\pm 20V, V_{DS}=0V$ | --- | --- | ± 100 | nA |
| gfs | Forward Transconductance | $V_{DS}=5V, I_D=15A$ | --- | 17 | --- | S |
| R_g | Gate Resistance | $V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$ | --- | 3.2 | --- | Ω |
| Q_g | Total Gate Charge (4.5V) | $V_{DS}=48V, V_{GS}=4.5V, I_D=12A$ | --- | 12.6 | --- | nC |
| Q_{gs} | Gate-Source Charge | | --- | 3.2 | --- | |
| Q_{gd} | Gate-Drain Charge | | --- | 6.3 | --- | |
| $T_{d(on)}$ | Turn-On Delay Time | $V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega, I_D=10A$ | --- | 8 | --- | ns |
| T_r | Rise Time | | --- | 14.2 | --- | |
| $T_{d(off)}$ | Turn-Off Delay Time | | --- | 24.4 | --- | |
| T_f | Fall Time | | --- | 4.6 | --- | |
| C_{iss} | Input Capacitance | $V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$ | --- | 1378 | --- | pF |
| C_{oss} | Output Capacitance | | --- | 86 | --- | |
| C_{rss} | Reverse Transfer Capacitance | | --- | 64 | --- | |

Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|----------|--|---|------|------|------|------|
| I_S | Continuous Source Current ^{1,5} | $V_G=V_D=0V$, Force Current | --- | --- | 30 | A |
| I_{SM} | Pulsed Source Current ^{2,5} | | --- | --- | 60 | A |
| V_{SD} | Diode Forward Voltage ² | $V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$ | --- | --- | 1.2 | V |

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=22.6A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

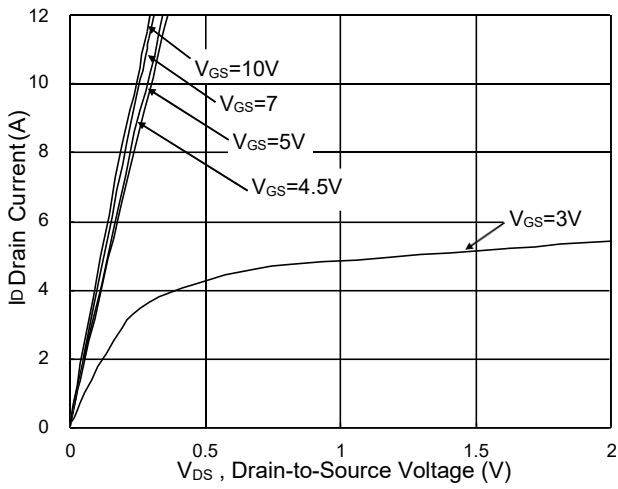


Fig.1 Typical Output Characteristics

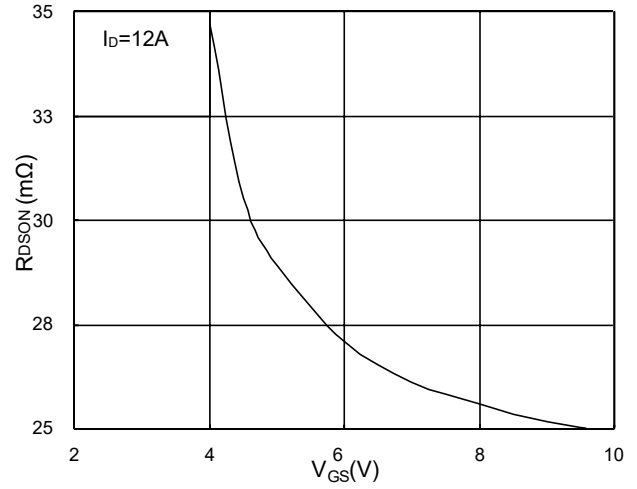


Fig.2 On-Resistance v.s Gate-Source

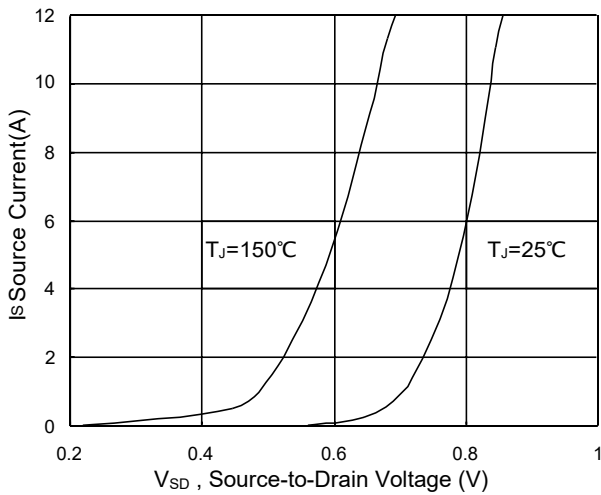


Fig.3 Forward Characteristics of Reverse

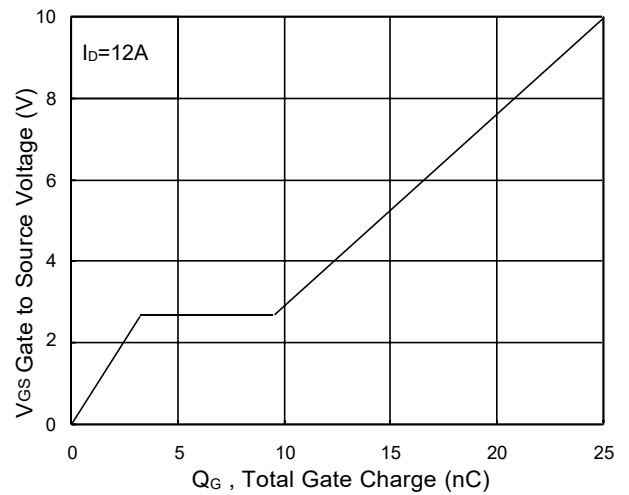


Fig.4 Gate-Charge Characteristics

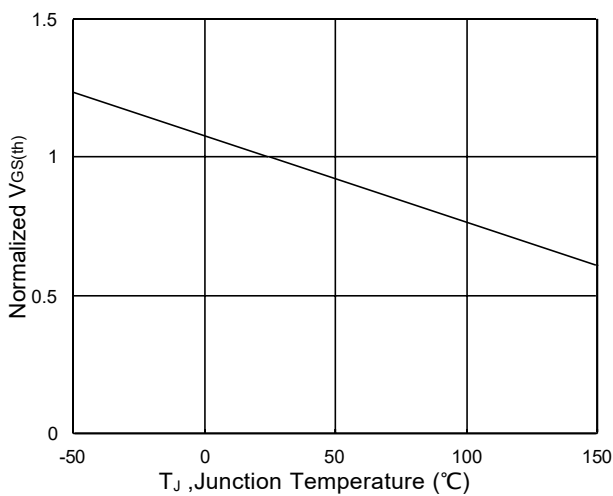


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

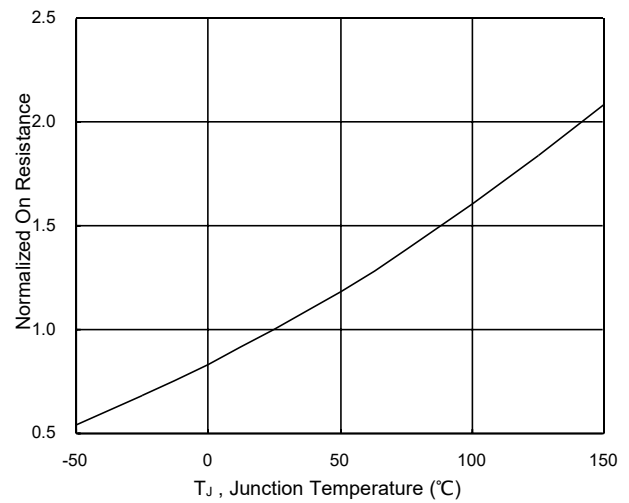
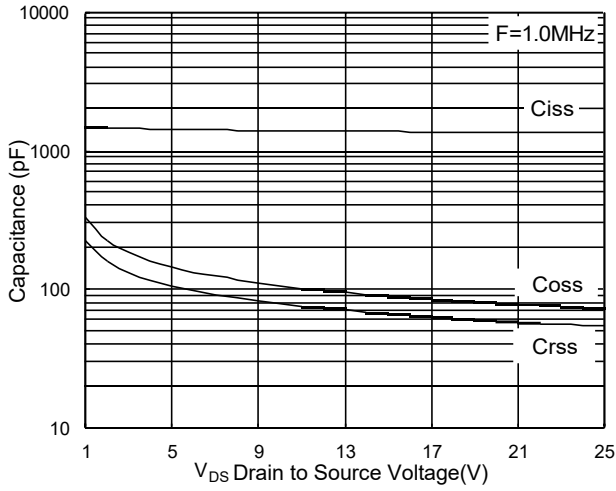
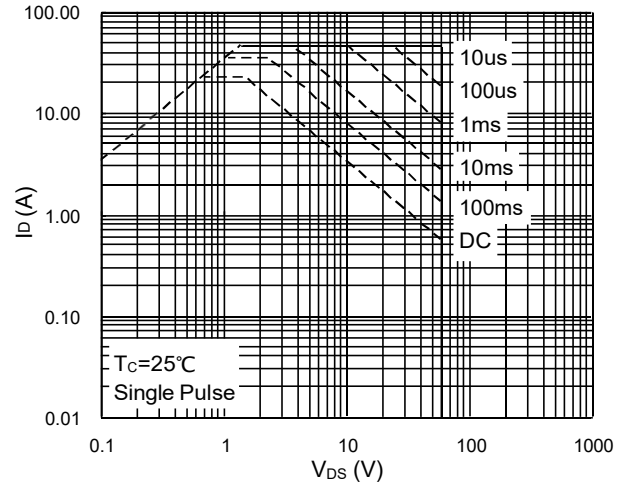
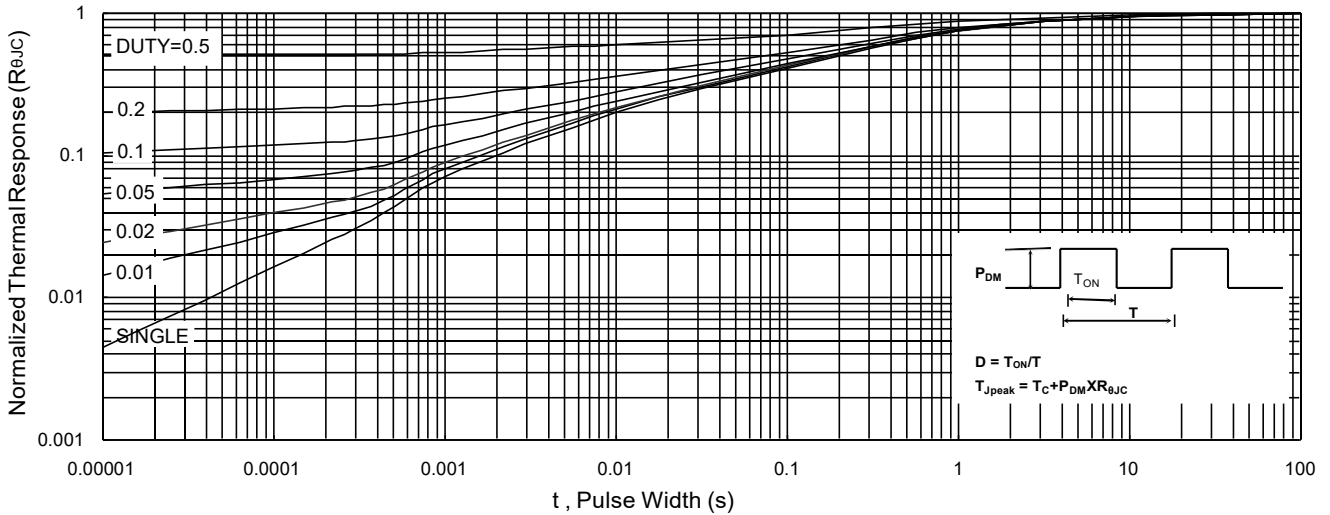
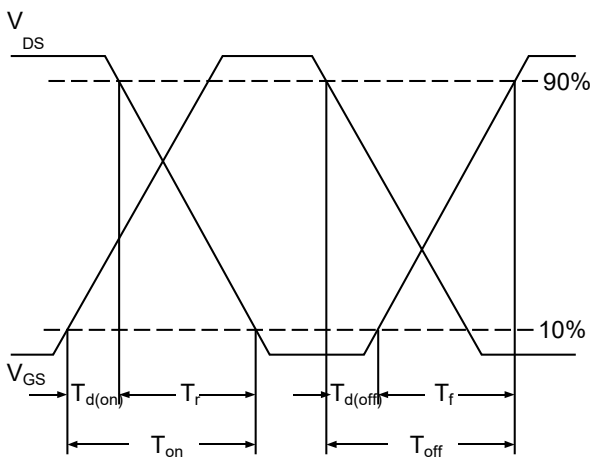
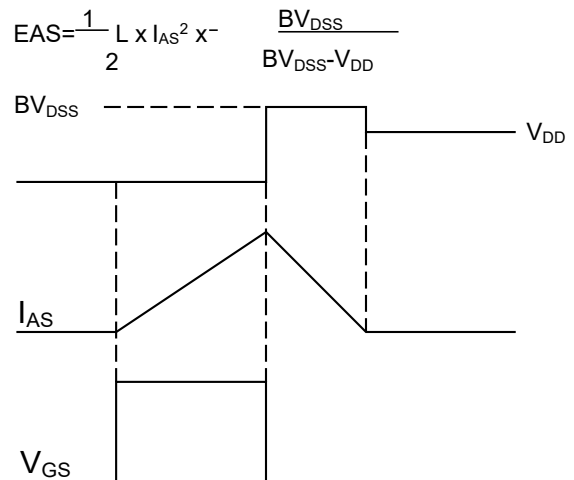


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

N-Ch 60V Fast Switching MOSFETs

Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform

Package Mechanical Data- PDFN3.3X3.3-8L
